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""Study of Static Noise Margin, Cell Stability and Influence of Electron Beam on Sub-30 nm SRAM Using SEM-Based Nanoprobing with 8 Nanoprobes""""Leaky Device Channel Anomaly Identification and Case Study by Nano-Probing Technique, Curve Fitting, and Model Analysis""; ""Photon Based Techniques: An Understanding""; ""Photon Emission Spectra of FETs as Obtained by InGaAs Detector""; ""Near-Infrared Photon Emission Spectroscopy Trends in Scaled SOI Technologies""
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